

# **TF2007U** Half-Bridge Gate Driver

#### **Features**

- Floating high-side driver in bootstrap operation to 200V
- Drives two N-channel MOSFETs or IGBTs in a half bridge configuration
- Designed for enhanced performance in noisy motor applications
- 290mA source/600mA sink output current capability
- Outputs tolerant to negative transients
- Internal dead time of 420ns to protect MOSFETs
- Wide low side gate driver supply voltage: 10V to 20V
- Logic input (HIN and LIN\*) 3.3V capability
- Schmitt triggered logic inputs
- Undervoltage lockout for V<sub>cc</sub> (logic and low side supply)
- Extended temperature range: -40°C to +125°C

### Description

The TF2007U is a high voltage, high speed gate driver capable of driving N-channel MOSFETs and IGBTs in a half bridge configuration. TF Semiconductors's high voltage process enables the TF2007U high side to switch to 200V in a bootstrap operation.

The TF2007U logic inputs are compatible with standard TTL and CMOS levels (down to 3.3V) to interface easily with controlling devices. The driver outputs feature high pulse current buffers designed for minimum driver cross conduction. TF2007U has a fixed internal deadtime of 420ns (typical).

The TF2007U is offered in a SOIC-8(N) package and operates over an extended -40  $^{\circ}$ C to +125  $^{\circ}$ C temperature range.

## **Applications**

- Motor Controls
- DC-DC Converters
- AC-DC Inverters
- Motor Drives



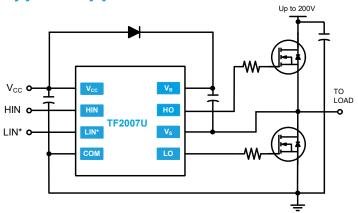
SOIC-8(N)

## **Ordering Information**

Year Year Week Week

PART NUMBER	PACKAGE	PACK / Qty	MARK
TF2007U-TAU	SOIC-8(N)	Tube / 100	
TF2007U-TAH	SOIC-8(N)	T&R / 2500	TF2007U
L		1	

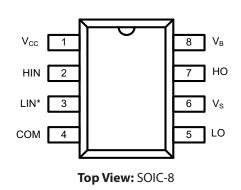
## **Typical Application**





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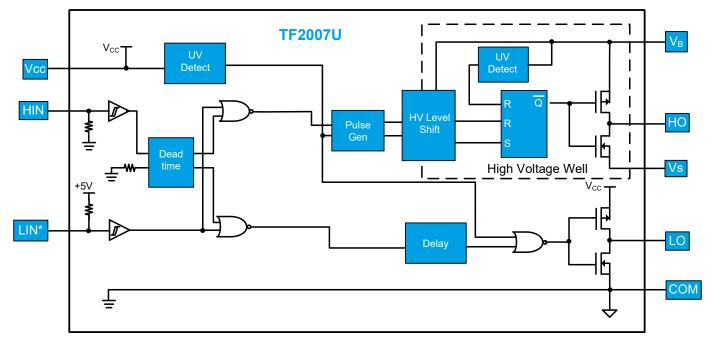


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## **Pin Descriptions**

PIN NAME	PIN NUMBER	PIN DESCRIPTION
V <sub>cc</sub>	1	Logic and low side supply
HIN	2	Logic input for high-side gate driver output in phase with HO
LIN*	3	Logic input for low-side gate driver output out of phase with LO
СОМ	4	Low-side and logic return
LO	5	Low-side gate drive output
V <sub>s</sub>	6	High-side floating supply return
НО	7	High-side gate drive output
V <sub>B</sub>	8	High-side floating supply

## **Functional Block Diagram**



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## Absolute Maximum Ratings (NOTE1)

$V_{\rm B}$ - High side floating supply voltage0.3V to +224V
$V_s$ - High side floating supply offset voltage $V_B$ -24V to $V_B$ +0.3V
$V_{Ho}$ -Highside floating output voltageV <sub>s</sub> -0.3V to V <sub>B</sub> +0.3V
$dV_{\rm s}/dt$ - Offset supply voltage transient50 V/ns

V <sub>cc</sub> - Low-side fixed supply voltage	0.3V to +24V
V <sub>10</sub> - Low-side output voltage	0.3VtoV <sub>cc</sub> +0.3V
V <sub>IN</sub> -Logic input voltage (HIN and LIN*)	cc

**NOTE1** Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

$P_D$ - Package power dissipation at $T_A \le 25 \text{ °C}$ SOIC-80.625W
SOIC-8(N) Thermal Resistance <i>(NOTE2)</i> θ <sub>JA</sub> 200 °C/W
T <sub>J</sub> - Junction operating temperature+150 °C T <sub>L</sub> - Lead Temperature (soldering, 10 seconds)+300 °C T <sub>stg</sub> - Storage temerature55 to 150 °C

**NOTE2** When mounted on a standard JEDEC 2-layer FR-4 board.

## **Recommended Operating Conditions**

Symbol	Parameter	MIN	МАХ	Unit
V <sub>B</sub>	High side floating supply absolute voltage	V <sub>s</sub> + 10	V <sub>s</sub> + 20	V
V <sub>s</sub>	High side floating supply offset voltage	NOTE3	200	V
V <sub>HO</sub>	High side floating output voltage	Vs	V <sub>B</sub>	V
V <sub>cc</sub>	Low side fixed supply voltage	10	20	V
V <sub>LO</sub>	Low side output voltage	0	V <sub>cc</sub>	V
V <sub>IN</sub>	Logic input voltage (HIN and LIN*)	0	5	V
T <sub>A</sub>	Ambient temperature	-40	125	°C

**NOTE3** Logic operational for VS of -5V to +200V.



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## DC Electrical Characteristics (NOTE4)

 $V_{\text{BIAS}}(V_{\text{CC}},V_{\text{BS}})$  = 15V,  $T_{\text{A}}$  = 25 °C , unless otherwise specified.

Symbol	Parameter	Conditions	MIN	ТҮР	МАХ	Unit
V <sub>IH</sub>	Logic "1" (HIN) & Logic "0" (LIN*) input voltage	$V_{cc} = 10V \text{ to } 20V$	2.5			
V <sub>IL</sub>	Logic "0" (HIN) & Logic "1" (LIN*) input voltage	NOTE 5			0.8	V
V <sub>OH</sub>	High level output voltage, V <sub>BIAS</sub> - V <sub>O</sub>	$I_0 = 2mA$		0.05	0.2	
V <sub>OL</sub>	Low level output voltage, V <sub>o</sub>	$I_0 = 2mA$		0.02	0.1	
I <sub>LK</sub>	Offset supply leakage current	VB = VS = 200V			50	
I <sub>BSQ</sub>	Quiescent V <sub>BS</sub> supply current	$V_{IN} = 0V \text{ or } 5V$		7		
I <sub>ccq</sub>	Quiescent V <sub>cc</sub> supply current	$V_{IN} = 0V \text{ or } 5V$		350	500	μA
I <sub>IN+</sub>	Logic "1" input bias current	$HIN = 5V, LIN^* = 0V$		3	10	
I <sub>IN-</sub>	Logic "0" input bias current	$HIN = 0V, LIN^* = 5V$			5	
$V_{CCUV+}$	V <sub>cc</sub> supply under-voltage positive going threshold		8.0	8.9	9.8	
V <sub>CCUV-</sub>	V <sub>cc</sub> supply under-voltage negative going threshold		7.4	8.2	9.0	V
$V_{\rm BSUV+}$	V <sub>BS</sub> supply under-voltage positive going threshold			6.3		V
V <sub>BSUV-</sub>	V <sub>BS</sub> supply under-voltage negative going threshold			5.2		V
I <sub>O+</sub>	Output high short circuit pulsed current	$V_{o} = 0V$ , PW $\leq 10 \ \mu s$	130	290		
I <sub>0-</sub>	Output low short circuit pulsed current	$V_{o} = 15V$ , PW $\leq 10 \ \mu s$	270	600		mA

**NOTE4** The  $V_{INV}$   $V_{TIV}$  and  $I_{INV}$  parameters are applicable to the two logic input pins: HIN and LIN\*. The  $V_o$  and  $I_o$  parameters are applicable to the respective output pins: HO and LO **NOTE5** For optimal operation, it is recommended that the input pulse (to HIN and LIN\*) should have an amplitude of 2.5V minimum with a pulse width of 800ns minimum.

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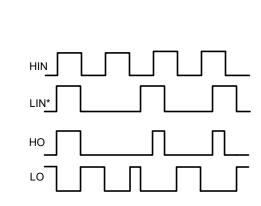
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# **AC Electrical Characteristics** $V_{BIAS}(V_{CC'}, V_{BS}) = 15V, C_{L} = 1000 \text{ pF}, \text{ and } T_{A} = 25 \text{ °C}$ , unless otherwise specified.

Symbol	Parameter	Conditions	MIN	ТҮР	MAX	Unit
t <sub>on</sub>	Turn-on propagation delay	$V_s = 0V$		100	200	
t <sub>off</sub>	Turn-off propagation delay	V <sub>s</sub> =200V		100	200	
t <sub>DM</sub>	Delay matching, HS & LS turn-on/turn-off				50	
t <sub>r</sub>	Turn-on rise time			70	150	ns
t <sub>r</sub>	Turn-off fall time	$V_s = 0V$		35	90	
t <sub>DT</sub>	Deadtime: t <sub>DT LO-HO</sub> & t <sub>DT HO-LO</sub>		300	420	650	

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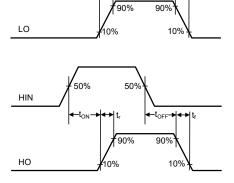
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**Timing Waveforms** 

Figure 1. Input / Output Timing Diagram



50%

↔ t<sub>r</sub>

50%

-t<sub>ON</sub>

LIN\*

Figure 2. Switching Time Waveform Definitions

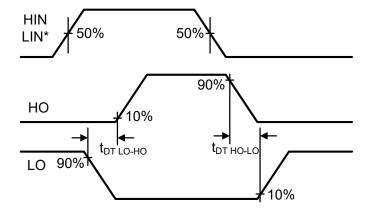


Figure 3. Deadtime Waveform Definitions

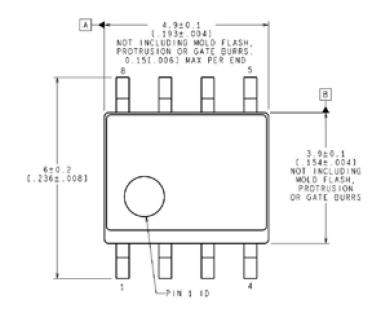
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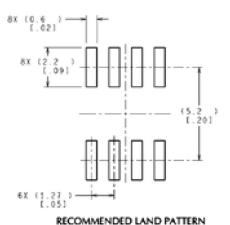


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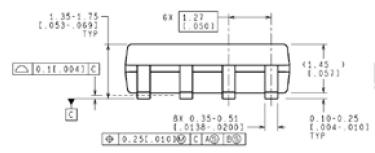
## Package Dimensions (SOIC-8 N)

Please contact support@telefunkensemi.com for package availability.



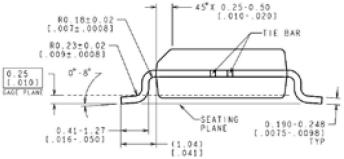


RECONTRACTOR DUTO FATERA



NOTES: UNLESS OTHERWISE SPECIFIED

1. REFERENCE JEDEC REGISTRATION MS-012, VARIATION AA.



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#### Half-Bridge Gate Driver

Rev.	Change	Owner	Date
1.0	First release, AI datasheet	Keith Spaulding	2/5/2019
1.1	Addition of Note 5	Duke Walton	2/7/2020

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